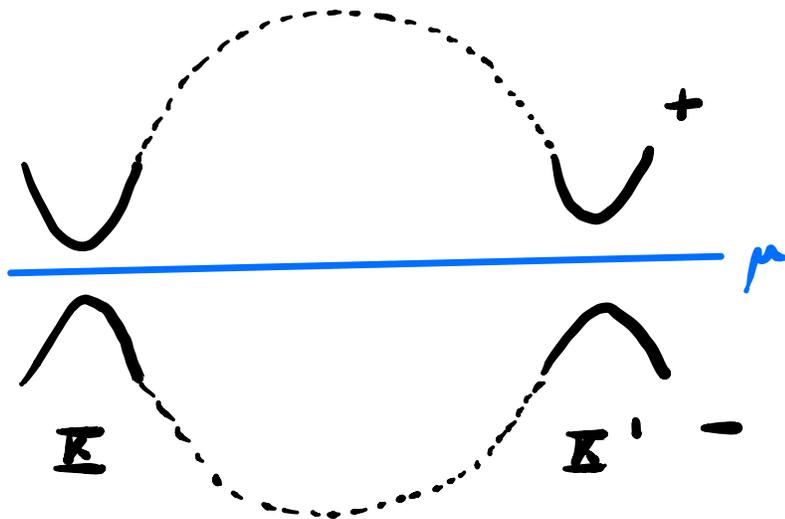


④ Quantum anomalous Hall insulator

a.n.a. } Chern insulator
 } Haldane "

2D insulator w/ nonzero and quantized Hall conductivity, in the absence of a magnetic field.

4.1 Graphene (spinless)



$$\ln(\vec{k}) = \vec{d}(\vec{k}) \cdot \vec{\sigma}$$

↑ sublattice

* Chern # of occupied band:

$$C_- = \frac{1}{2\pi} \int_{\text{BZ}} dk_x dk_y B_{xy,-}(\vec{k})$$

where (cf hw #3)

$$B_{xy,-}(\vec{k}) = \frac{1}{2} \hat{d} \cdot \left(\frac{\partial \hat{d}}{\partial k_x} \times \frac{\partial \hat{d}}{\partial k_y} \right)$$

* Calculation of C_- from the low-energy theory:

$$d_{\mathbf{I}}(\vec{q}) = \vec{d}_{\mathbf{I}}(\vec{q}) \cdot \vec{\sigma}$$

where

$$d_{\mathbf{I},x}(\vec{q}) = v q_x$$

$$d_{\mathbf{K}, y}(\vec{q}) = v q_z$$

$$d_{\mathbf{K}, z}(\vec{q}) = \underbrace{m_{\mathbf{K}}}$$

↑
independent of \vec{q} .

$$h_{\mathbf{K}'}(\vec{q}) = \vec{d}_{\mathbf{K}'}(\vec{q}) \cdot \vec{q}$$

$$d_{\mathbf{K}', x}(\vec{q}) = -v q_x$$

$$d_{\mathbf{K}', y}(\vec{q}) = v q_z$$

$$d_{\mathbf{K}', z}(\vec{q}) = \underbrace{m_{\mathbf{K}'}}$$

↑
independent of \vec{q}

$$C_- = C_-^{(\mathbb{K})} + C_-^{(\mathbb{K}')}$$

"partial Chern # 5"

$$C_-^{(\lambda)} = \frac{1}{2} \int_{-\infty}^{\infty} dq_x dq_y B_{xy, -}^{(\lambda)} \left(\vec{q} \right)$$

where $\lambda = \mathbb{K}, \mathbb{K}'$

$$C_-^{(\mathbb{K})} = \frac{1}{2} \text{sgn} (m_{\mathbb{K}})$$

$$C_-^{(\mathbb{K}')} = -\frac{1}{2} \text{sgn} (m_{\mathbb{K}'})$$

Then,

$$C_- = \frac{1}{2} \left[\text{sgn}(m_{\mathbb{Z}}) - \text{sgn}(m_{\mathbb{Z}'}) \right]$$

* Recall:

$$m_{\mathbb{Z}} = \underbrace{\mu_{\mathbb{Z}}}_{\substack{\uparrow \\ \text{Semenoff} \\ \text{mass}}} + \underbrace{w_{\mathbb{Z}}}_{\substack{\uparrow \\ \text{Haldane} \\ \text{mass}}}$$

$$m_{\mathbb{Z}'} = \mu_{\mathbb{Z}} - w_{\mathbb{Z}}$$

If TRS is present, $w_{\mathbb{Z}} = 0$ and

hence $\text{sgn}(m_{\mathbb{Z}}) = \text{sgn}(m_{\mathbb{Z}'})$

$\Rightarrow \boxed{C_- = 0}$ for Semenoff insulator.

This insulator is adiabatically connected to vacuum:

Keep $\mu_z \neq 0$ while taking all interatomic hoppings to zero. The final state is a vacuum. The energy gap remained always open in the process.

If TRS is broken (but SIS is preserved):

$$\mu_z = 0$$

$$w_z \neq 0$$

$$\Rightarrow m_{\mathbf{I}} = w_z = -m_{\mathbf{B}}!$$

$$\Rightarrow \text{sgn}(m_{\mathbb{I}}) = -\text{sgn}(m_{\mathbb{I}'})$$

$$\Rightarrow \boxed{C_- = \text{sgn}(m_{\mathbb{I}}) = \pm 1}$$

Haldane insulator is topologically nontrivial.

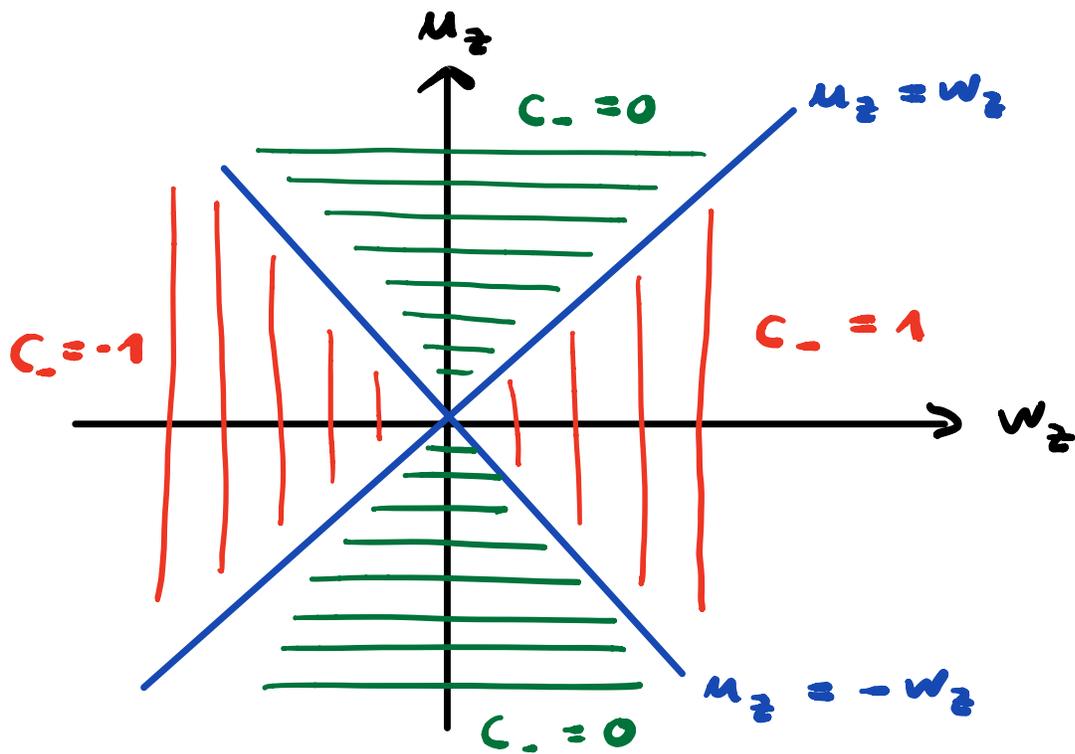
$$\sigma_{xy} = \frac{e^2}{h} C_- \neq 0.$$

If both TRS and SIS are broken,

$$m_{\mathbb{I}} = \mu_z + w_z$$

$$m_{\mathbb{I}'} = \mu_z - w_z$$

Topological phase diagram:

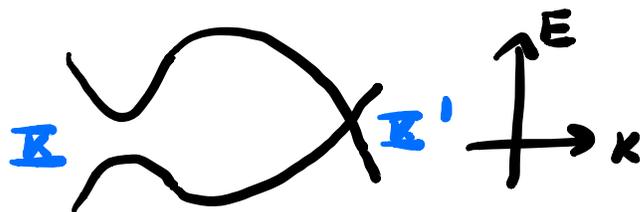


— $C_- = 0$

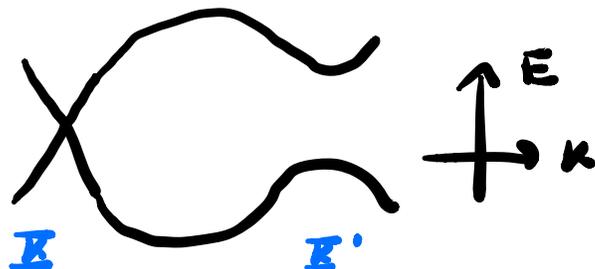
— $C_- \neq 0$

— gap closes (TPT)

$$u_z = w_z \Rightarrow m_{\mathbb{R}} \neq 0, m_{\mathbb{R}'} = 0$$



$$\mu_3 = -w_2 \Rightarrow m_{\mathbb{Z}'} \neq 0, m_{\mathbb{Z}} = 0$$



* Geometric interpretation
of Chern #: :

$$h(\vec{k}) = \vec{d}(\vec{k}) \cdot \vec{\sigma}$$

$C_- = \#$ of times $\hat{d}(\vec{k})$

covers the unit sphere as

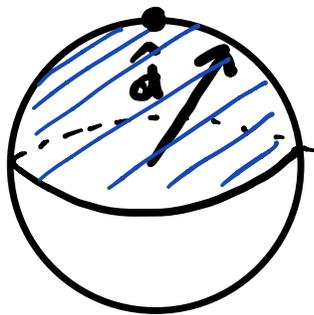
\vec{k} is varied within the 1st

$B\mathbb{Z}$. "winding #"

(i) Semiconducting insulator:

$d_z(\vec{k})$ doesn't change
sign with \vec{k} .

$$[\text{sgn}(m_{\mathbb{Z}}) = \text{sgn}(m_{\mathbb{Z}'})]$$



case in which

$$d_z > 0.$$

\hat{d} only covers the
northern hemisphere.



$$d_x = \pm v q_x$$

$$d_y = v q_y$$

$$c_z = 0$$

(ii) Haldane insulator :

$d_z(\vec{k})$ has opposite sign
near \mathbb{K} and \mathbb{K}' valleys.

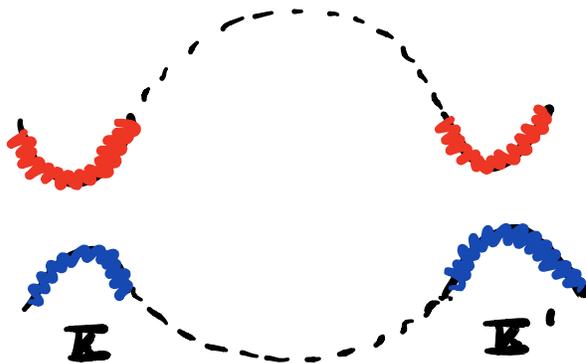


\hat{d} covers the whole
sphere

$$\Rightarrow |C_-| = 1$$

* Concept of "band inversion" :

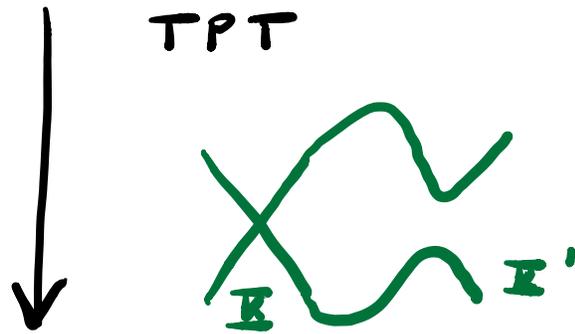
(i) Semiconducting insulator



— states with predominantly
A-like character

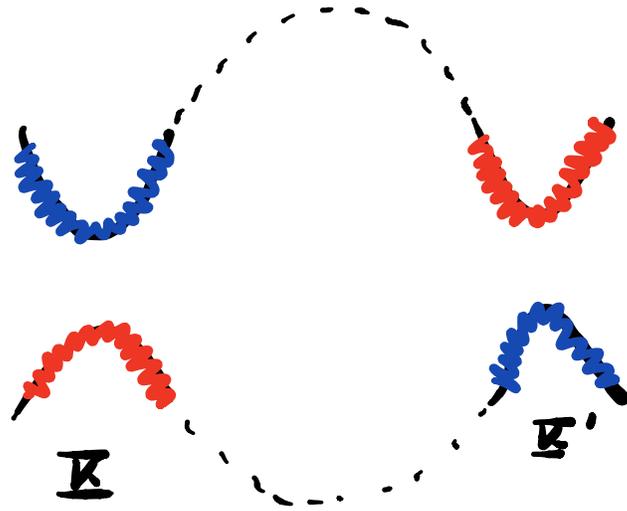
— states w/ predominantly
B-like character.

$$d_z \neq 0$$



Gap closing at E (say)

(ii) Haldane insulator



"Band inversion" at K

↑
 general mechanism for
 changing a topological
 invariant.

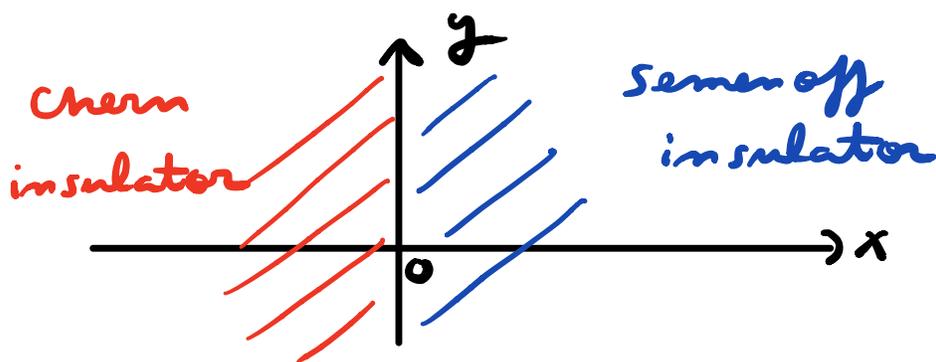
* Some caution words about
 low-energy calculation of C_2 :

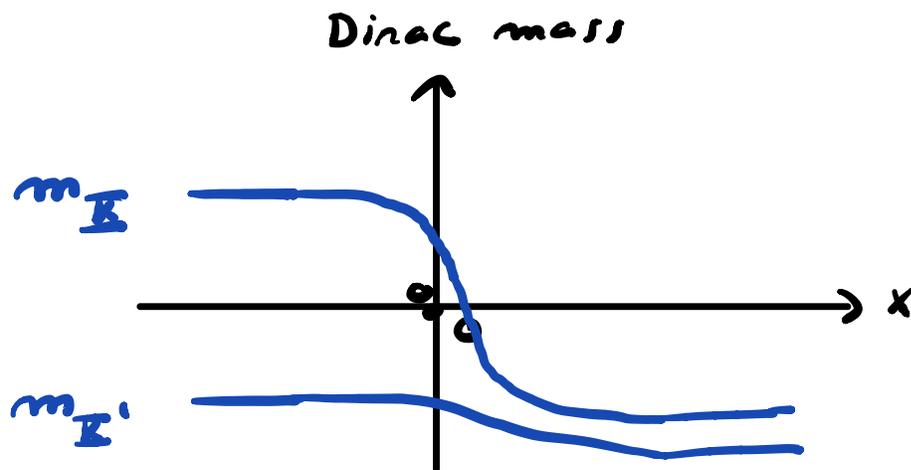
This method does not always
 work.

In general, one needs to consider the details of the high-energy electronic states in order to calculate C_- .

At any rate, the low-energy calculation of C_- is good if we want to compute the change of Chern # across a band inversion.

4.2 Edge states





$m_{\mathbb{I}}$ has a domain wall
at $x=0$.

Generalisation of Jackiw-Rebbi
mode to 2D?

$$h_{\mathbb{I}} = v (-i\sigma^x \partial_x - i\sigma^z \partial_y) + m_{\mathbb{I}}(x) \sigma^z$$

$$[h_{\mathbb{I}}, p_y] = 0$$

$$\hbar_{\mathbb{R}} \psi(x, y) = E \psi(x, y) \quad (1)$$

where

$$\psi(x, y) = e^{i \eta y} \phi(x) \quad (2)$$

η = momentum along y
= good quantum #

(1) and (2) :

$$\begin{aligned} & \nu \left(-i \sigma^x \partial_x + \sigma^z \eta + m_{\mathbb{R}} \sigma^z \right) \phi(x) \\ & = E_{\eta} \phi(x) \end{aligned}$$

At $\eta = 0$, the problem becomes familiar:

$$\underbrace{v (-i \sigma^x \partial_x + m_{\mathbb{K}} \sigma^z)}_{\substack{\uparrow \\ \text{1D Dirac} \\ \text{Hamiltonian} \\ \text{w/ domain wall}}} \phi(x)$$

$$= E_0 \phi(x)$$

We know that there's a zero-energy solution ($E_0 = 0$):

$$\phi_{\text{edge}}(x)$$

$$= \begin{pmatrix} 1 \\ -i \end{pmatrix} e^{\frac{1}{v} \int_0^x dx' m_{\mathbb{K}}(x')}$$

Exponentially localised at $x = 0$.

For $q \neq 0$:

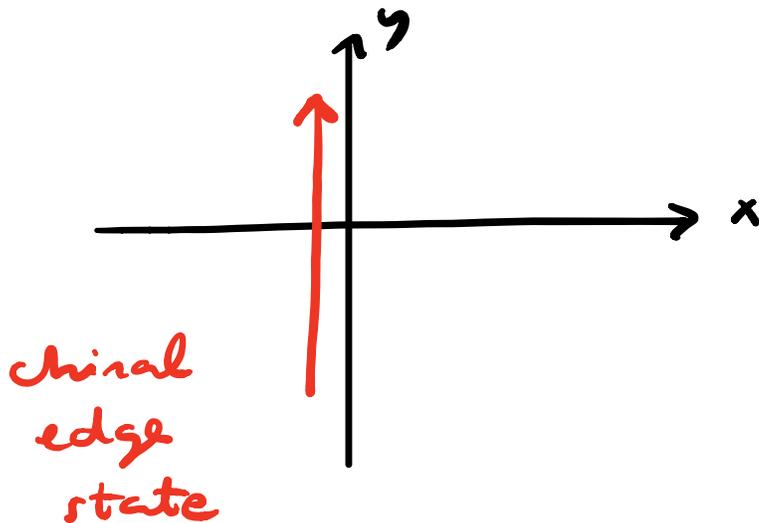
$$\psi_{\text{edge}}(x, y) = e^{iqy} \phi_{\text{edge}}(x)$$

Replace this in

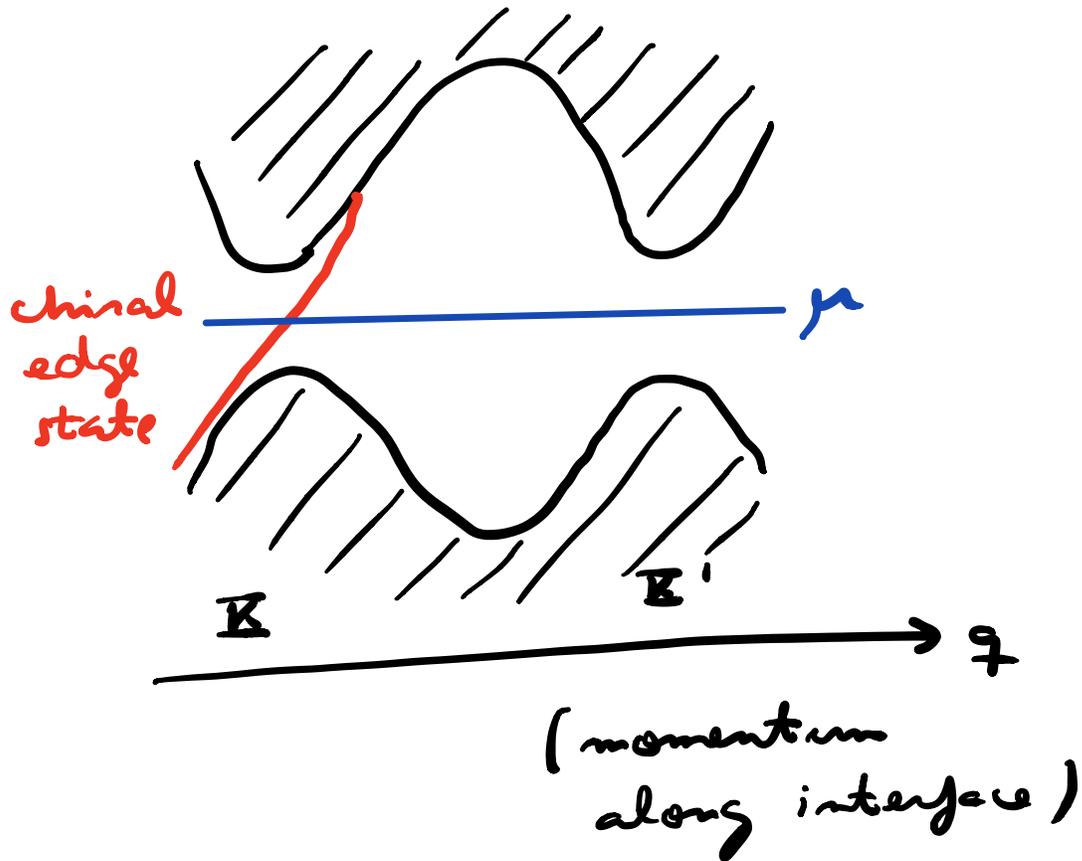
$$\ln_{\mathbb{R}} \psi(x, y) = E \psi(x, y),$$

to get

$$E = E_q = v q$$



Band structure :



"1D" unidirectional edge state.

Insulating bulk.

Conducting edge.

of edge states = $|C - 1|$

"bulk - boundary correspondence"

H.3 Experimental realisation

* Cold atoms in optical lattices:

G. Jotzu et al., Nature 515,
237 (2014)

* Magnetically doped Bi_2Se_3
thin films.

C.-Z. Chang et al.,
Science 340, 167 (2013)

* Essential ingredients:

(i) 2D insulator

(ii) Magnetism (to break TRS)

(iii) Spin-orbit coupling

(communicates broken TRS
from spin sector to orbital
sector)

* Possible applications

(i) Chiral edge states

→ interconnects in
integrated circuits.

(ii) Other.

* Current limitation:

bulk gaps are small

→ QAH phase is realized

only at low T .

In principle, there's no reason why this phase could not occur at room temperature. More research is needed.